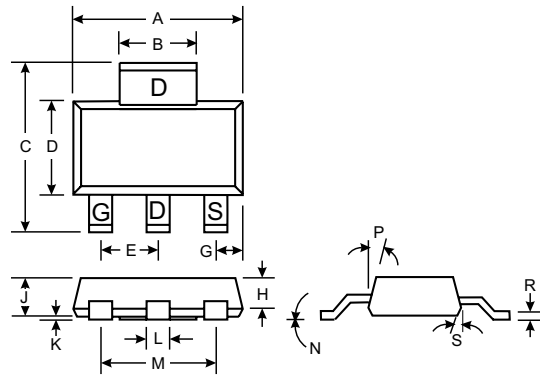


Features

- High Cell Density DMOS Technology
- Low On-State Resistance
- High Power and Current Capability
- Fast Switching Speed
- High Transient Tolerance



SOT-223		
Dim	Min	Max
A	6.30	6.71
B	2.90	3.10
C	6.71	7.29
D	3.30	3.71
E	2.22	2.35
G	0.92	1.00
H	1.10	1.30
J	1.55	1.80
K	0.025	0.102
L	0.66	0.79
M	4.55	4.70
N	—	10°
P	10°	16°
R	0.254	0.356
S	10°	16°
All Dimensions in mm		

Mechanical Data

- SOT-223 Plastic Case
- Terminal Connections: See Outline Drawing and Internal Circuit Diagram Above

Maximum Ratings 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current	I_D	±2.7 ±10	A
Maximum Power Dissipation	P_d	3.0 1.3 1.1	W
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	°C

Thermal Characteristics

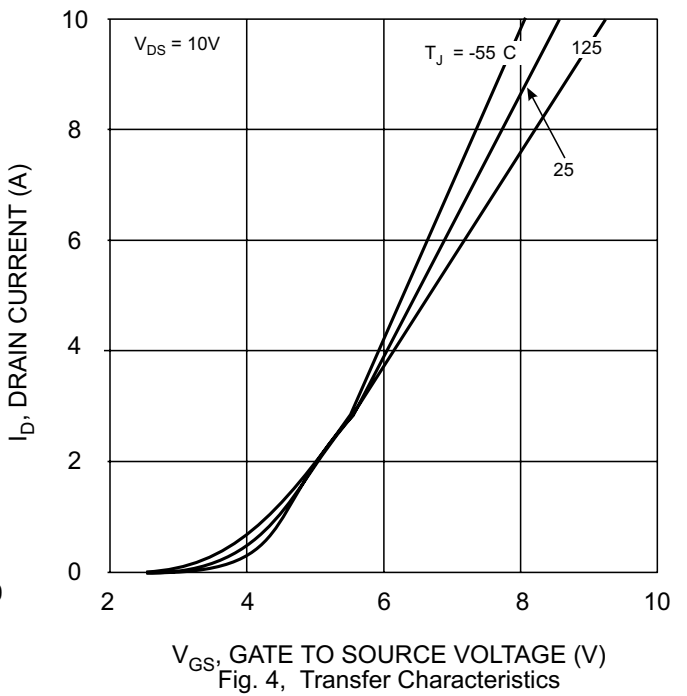
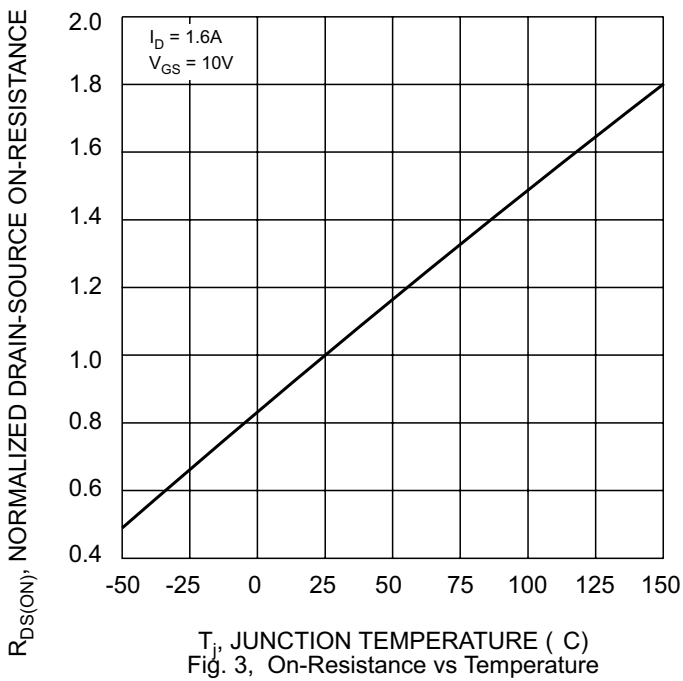
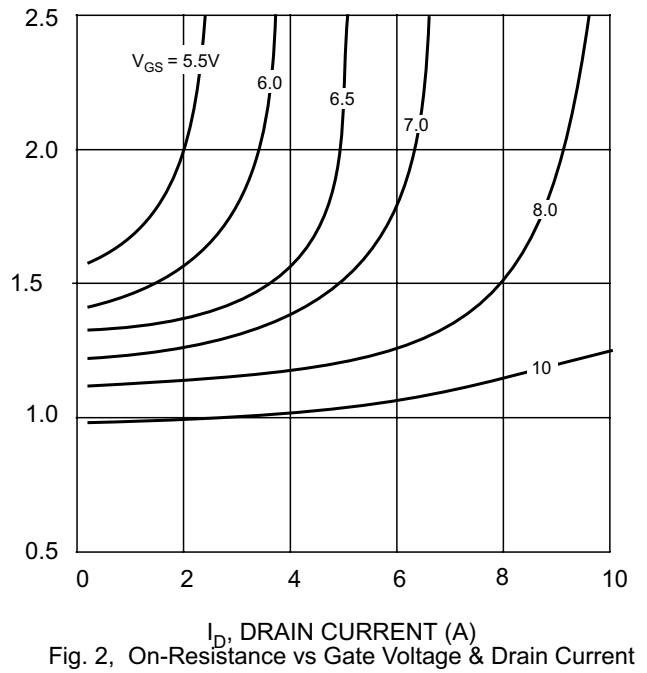
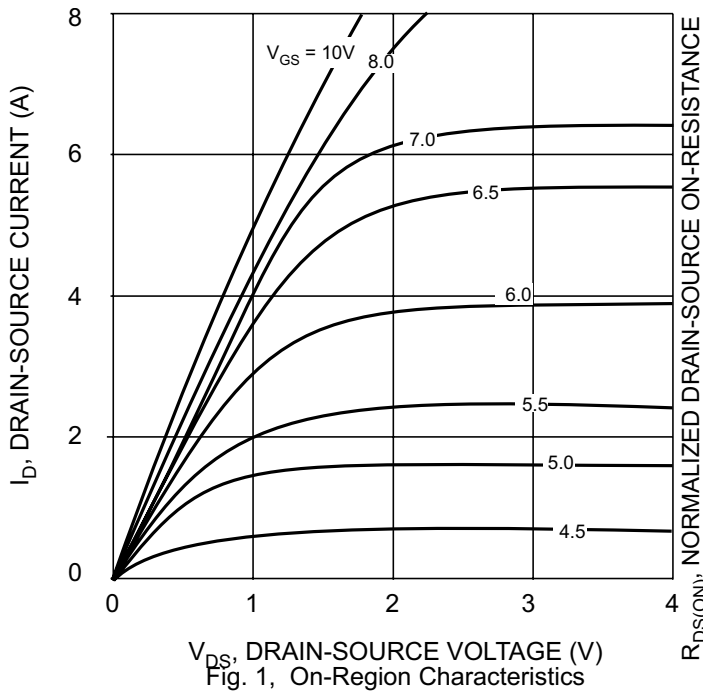
Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	42	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	12	°C/W

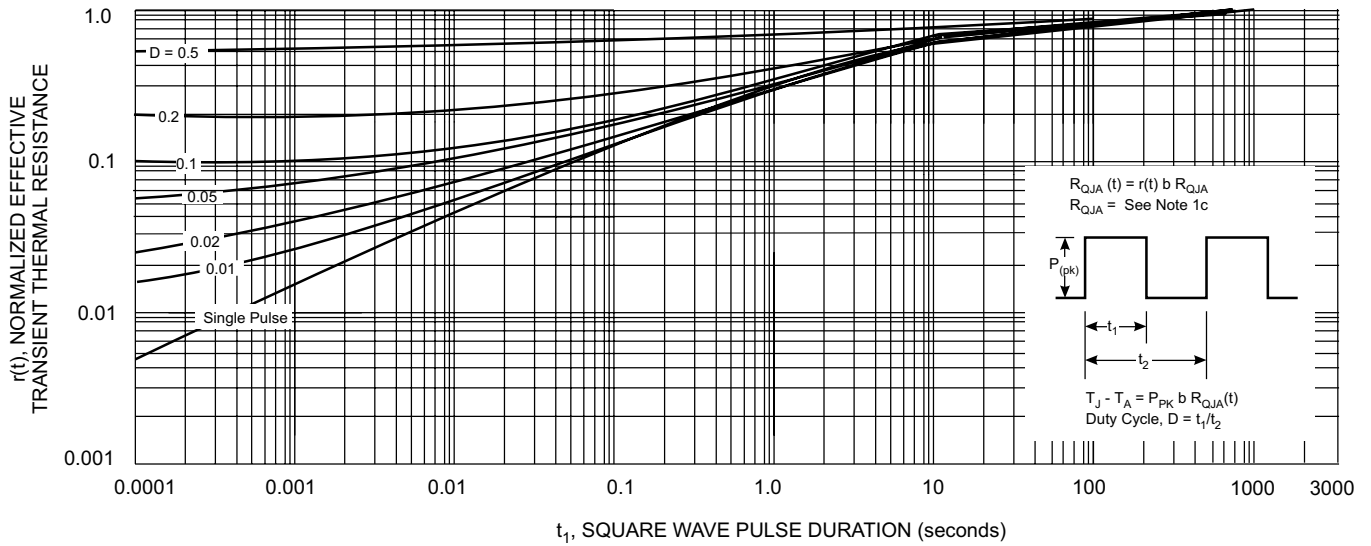
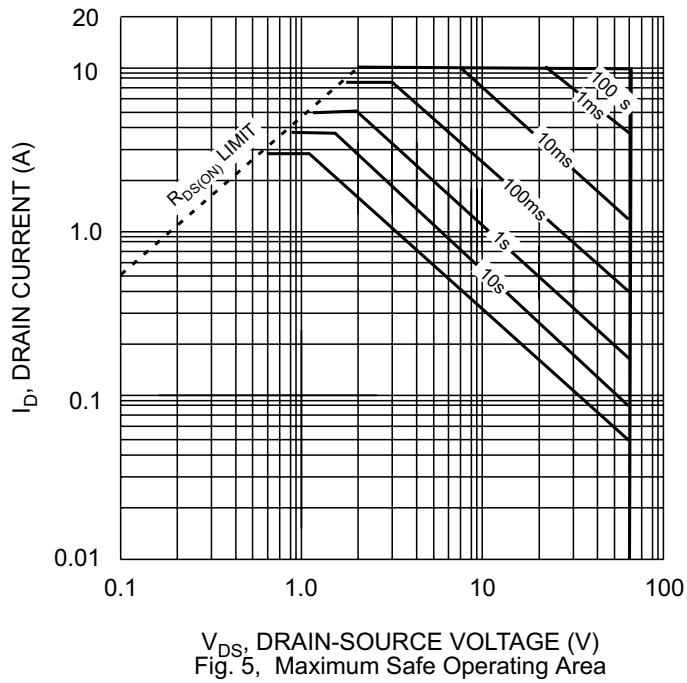
- Notes:
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
 - 1a. With 1 in² oz 2 oz. copper mounting pad $R_{\theta JA} = 42^\circ\text{C/W}$.
 - 1b. With 0.0066 in² oz 2 oz. copper mounting pad $R_{\theta JA} = 95^\circ\text{C/W}$.
 - 1c. With 0.0123 in² oz 2 oz. copper mounting pad $R_{\theta JA} = 110^\circ\text{C/W}$.

Electrical Characteristics 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_j = 125^\circ C$	I_{DSS}	—	—	25 250	μA	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V$
Gate-Body Leakage, Forward	I_{GSSF}	—	—	100	nA	$V_{GS} = 20V, V_{DS} = 0V$
Gate-Body Leakage, Reverse	I_{GSSR}	—	—	-100	nA	$V_{GS} = -20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.18	0.2	Ω	$V_{GS} = 10V, I_D = 1.6A$
Forward Transconductance	g_{FS}	—	2.0	—	m	$V_{DS} = 25V, I_D = 1.6A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	—	155	—	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{OSS}	—	60	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	15	—	pF	
SWITCHING CHARACTERISTICS (Note 2)						
Turn-On Delay Time	$t_{D(ON)}$	—	10	20	ns	$V_{DD} = 30V, I_D = 10A$ $V_{GEN} = 10V, R_{GEN} = 24\Omega$
Turn-On Rise Time	t_r	—	64	100	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	10	20	ns	
Turn-Off Fall Time	t_f	—	10	20	ns	
Total Gate Charge	Q_g	—	5.0	11	nC	$V_{DS} = 48V, I_D = 10A.$ $V_{GS} = 10V$
Gate-Source Charge	Q_{gs}	—	1.2	3.1	nC	
Gate-Drain Charge	Q_{gd}	—	2.0	5.8	nC	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Max Continuous Drain-Source Diode Forward Current	I_S	—	—	2.7	A	
Max Pulsed Drain-Source Diode Forward Current	I_{SM}	—	—	22	A	
Drain-Source Diode Forward Voltage (Note 2)	V_{SD}	—	0.95	1.6	V	$V_{GS} = 0V, I_S = 2.7A$
Reverse Recovery Time	t_{rr}	—	—	140	ns	$V_{GS} = 0V, I_F = 10A$ $di_F / dt = 100A/\mu s$

Notes: 2. Pulse Test: Pulse width $\leq 300\mu s$, duty cycle $\leq 2.0\%$.





Remark: Thermal characterization performed under conditions described in note 1c. Transient thermal response will change depending on the circuit board design.